CMOS LSI FM multiple tuner IC



Overview

LC01707PLF is a vehicle-mounted FM multiple tuner IC with FM-FE, IF, IF-Filter, PLL, FM-DEMO and LPF incorporated. An FM multiple tuner can be developed with this one chip. It makes up a small-sized FM multiple tuners which can be mounted on PND.

Functions

- It is the FM tuner IC exclusively for the FM multiple.
- Image reduction complex BPF is incorporated
- Narrow Band IF AGC is incorporated

- LNA is incorporated
- Wide / Narrow Band RF AGC is incorporated
- Image rejection is adopted
- DLL detection method is adopted for the FM detection circuit, and it is not necessary to adjust.
- LPF for the carrier removal is incorporated.
- IC requires fewer external components. • It is a BUS control tuner IC which can be controlled by controlled by I^2C BUS.

Specifications **Maximum Ratings** at $Ta = 25^{\circ}C$

maximum natings at 1a	-25 0			
Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V _{DD} max		4.3	V
Maximum input voltage	V _{DD} H		4.3	V
Maximum output voltage	V _{DD} L		4.3	V
Power dissipation	Pd max	Ta = 85°C *1	700	mW
Operating ambient	Topr		-40 to 85	°C
Storage temperature	Tstg		-55 to 150	°C
Maximum junction temperature	Tj max		150	°C

*1: Board size: 80mm × 70mm × 1.6mm Glass epoxy double-sided board

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Recommended Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage range	V _{DD}		3.0 to 3.6	V
Recommended supply temperature	V _{DD}		3.3	V

Electrical Characteristics at Ta = 25°C, V_{DD} = 3.3V,

fc = 83MHz, VIN=60dBµVEMF, fm=1kHz, Audio filter: HPF=100Hz, LPF=15kHz

Resister setting: IF AGC (02h) =6(110), RF AGC (00h) =0(0000)

DLL demodulator loop gain setting (09h) = 1(01), Mono multi center setting (09h) = 7(0111)

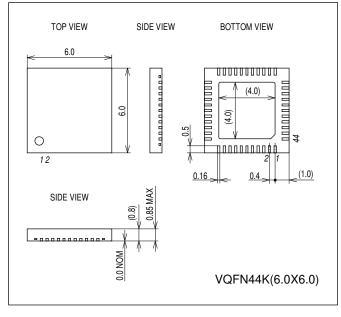
Parameter	Cumbol	Conditions		Ratings		Unit	
Parameter	Symbol	Conditions	min	typ	max		
Practical sensitivity 1 (S/N30dB)	SN30	22.5kHz dev, fm=1kHz, S/N=30dB input level		12	20	dBµEMF	
Practical sensitivity 2 (S/N10dB)	SN10	7.5kHz dev, fm=76kHz, S/N=10dB input level		27		dBµEMF	
		*1					
S/N1	SN1	22.5kHz dev, fm=1kHz	34	44		dB	
S/N2	SN2	7.5kHz dev, fm=76kHz *1		21		dB	
Total harmonic distortion rate 1	THD_1	22.5kHz dev, fm=1kHz		0.5		%	
Total harmonic distortion rate 2	THD_2	75.0kHz dev, fm=1kHz		0.5		%	
AM suppression ratio	AMR	AM 30% mod	34	44		dB	
Image rejection ratio	IMR	22.5k\Hz dev, fm=1kHz		32		dB	
Audio output level 1	AD01	7.5kHz dev, fm=1kHz *1	26	39	70	mVrms	
Audio output level 2	AD02	7.5kHz dev, fm=76kHz *1	15	23	41	mVrms	
Consumption current	IDD	No signal input		106	170	mA	

*1: Audio filter: HPF=100Hz, LPF=OFF

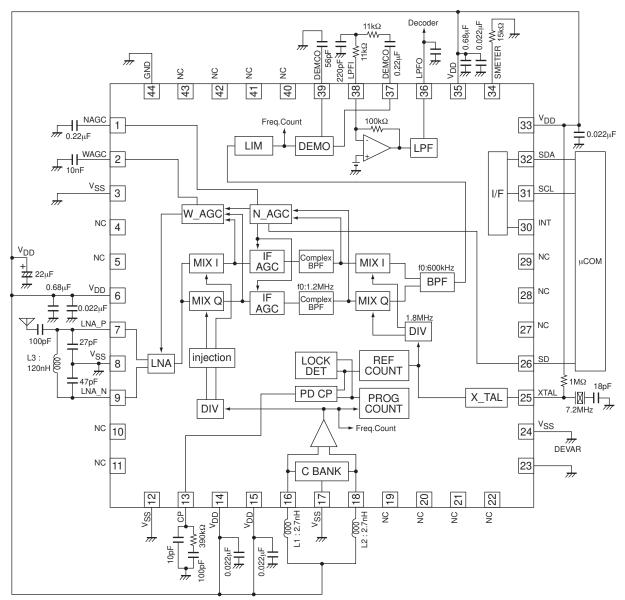
Package Dimensions

unit : mm (typ)

3408



Example of applied circuit (constant is tentative)



* Culprits oscillation circuit is used in this IC as a crystal oscillation circuit. Caution is required for layout of the board because oscillation between pin25 and power source and GND line.

* The margin of crystal oscillation changes due to the combination of the IC, a crystal oscillator and a board layout. This independent IC does not quarantine the oscillation operation.

* This IC uses the signal of FM band frequency (VCO divided into 1/4) which leaks into ANT pin. If the VCO leakage affects the performance of the system, make sure to connect an isolator on ANT pin path.

Component	Parameter	Value	Туре	Supplier
L1/L2	Local OSC coil	2.7nH	C2012H-2N7D-RD	SAGAMI
L3	Differential input coil	120nH	C2012C-R12G-RC	SAGAMI
X1	Crystal	7.2MHz	SMD-49	KDS
			AT-49	KDS
			EXS00A-A01145	NDK
			EXS00A-A01146	NDK

Pin Description

Pin No.	Pin name	I/O	Function	
1	NAGC	0	Narrow band AGC detection capacitance connecting pin	
2	WAGC	0	Wide band AGC detection capacitance connecting pin	
3	V _{SS}	Р	GND pin for IF	
4	NC	-		
5	NC	-		
6	V _{DD}	Р	Supply pin for LNA	
7	LNA_A	I	LNA +input pin	
8	V _{SS}	Р	GND pin for LNA	
9	LNA_N	I	LNA –input pin	
10	NC	-		
11	NC	-		
12	V _{SS}	Р	GND pin for 1 st Mixer	
13	СР	0	PLL charge pump capacitance connecting pin	
14	V _{DD}	Р	Supply pin 1 st Mixer	
15	V _{DD}	Р	Supply pin for local oscillation	
16	LO_1	0	Inductor connecting pin for local oscillation	
17	V _{SS}	Р	GND pin for local oscillation	
18	LO_2	0	Inductor connecting pin for local oscillation	
19	NC	-		
20	NC	-		
21	NC	-		
22	NC	-		
23	DEVER	I	Device address setting pin	
24	V _{SS}	Р	GND pin for PLL and logic	
25	XTAL	I	Crystal resonator connecting pin (Clock input pin)	
26	SD	0	Station detector pin	
27	NC	-		
28	NC	-		
29	NC	-		
30	INT	0	Test pin	
31	SCL	I	Serial data clock input	
32	SDA	I	serial data input-output	
33	V _{DD}	Р	Supply pin for PLL and logic	
34	SMETER	0	S-meter output	
35	V _{DD}	Р	Supply pin for IF	
36	LPFO	0	Demodulation output (after band limitation)	
37	DEMOO	0	Demodulation output	
38	LPFI	1	Demodulation signal input pin	
39	DEMOC	0	Capacitance connecting pin for demodulation detection	
40	NC	-		
41	NC	-		
42	NC	-		
43	NC	-		
44	GND	Р	GND pin	

Pin Function

Pin No.	Pin name	Function	Equivalent circuit
1	NAGC	Narrow band AGC detection capacitor connection pin.	$V_{DD} \stackrel{\bullet}{\stackrel{\bullet}{\stackrel{\bullet}{\stackrel{\bullet}{\stackrel{\bullet}{\stackrel{\bullet}{\stackrel{\bullet}{\bullet$
2	WAGC	Wide band AGC detection capacitor connection pin.	
3	V _{SS}	GND pin for IF.	
4	NC	No connection.	
5	NC	No connection.	
6	V _{DD}	Supply pin for LNA.	
7	LNA_P	Pin 7 is + input pin for LNA.	עס ^ע מס ^ע מסע ש
8	V _{SS}	Pin 8 is GND pin for LNA.	
9	LNA_N	Pin 9 is - input pin for LNA.	
10	NC	No connection.	
11	NC	No connection.	
12	V _{SS}	GND pin 1st mixer for the 1 st mixer.	
13	СР	PLL charge pump capacitor connection pin.	$V_{DD} \stackrel{\bullet}{\rightarrow} V_{DD}$
14	V _{DD}	Supply pin for the 1 st mixer.	
15	V _{DD}	Supply pin for local oscillator.	
·			

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Pin No Pin name Function Equivalent circuit 16 LO_1 Pin 16 is inductor connection pin for local (17 (16)(18 17 VSS oscillator. LO_2 Pin 17 is GND pin for local oscillator. 18 Pin 18 is inductor connection pin for local ┨┠ -11 £ Ð oscillator. Cap Bank Cap ┨┠┯┨┣┫ ►ŀ To Pin13 ______ 200kΩ ______ 200kΩ Ļ 19 NC No connection. NC 20 No connection. 21 NC No connection. 22 NC No connection. DEVAR 23 Device address setting pin. VDD VDD w 500Ω 24 VSS PLL_logic GND pin. 25 XTAL Crystal oscillator connection pin (clock input VDD pin). ┨┣ $1M\Omega$ 5pF -₩ 33Ω 20pF 1MΩ ≩ 10pF 26 SD Station detector pin. 30 INT Test monitor pin. VDD VDD (30)26 27 NC No connection. NC 28 No connection. 29 NC No connection.

Continu	ed from prec	ceding page.	
Pin No.	Pin name	Function	Equivalent circuit
31	SCL	Serial data clock input.	V_{DD}
32	SDA	Serial data input/ output.	
33	V _{DD}	PLL_logic supply voltage pin.	
34	SMETER	S-meter output.	$\begin{array}{c} V_{DD} \\ V_{DD} \\ \downarrow \\ \downarrow \\ 34 \\ \downarrow \\ 500\Omega \\ \downarrow \\ \end{matrix}$
35	V _{DD}	IF supply voltage pin	
36	LPFO	Demodulator output (After band limit).	V_{DD} V_{DD} V_{DD} $4pF$ 36 $70k\Omega$ $70k\Omega$
37	DEMOO	Demodulator output.	V_{DD} V_{DD} V_{DD} 20.4pF $18.7k\Omega$ $19F$ $2k\Omega$ m
38	LPFI	Demodulator signal input pin.	VDD 38 500Ω 100kΩ 1pF

Continu	ied from prec	eding page.	
Pin No.	Pin name	Function	Equivalent circuit
39	DEMOC	Capacitor connection pin for demodulator detection.	$\begin{array}{c} 39 \\ \hline \\ $
40	NC	No connection.	
41	NC	No connection.	
42	NC	No connection.	
43	NC	No connection.	
44	GND	GND pin.	VSS (Pin_3) VSS (Pin_8) (Pin_12) VSS (Pin_17) VSS (Pin_24)

Communication specification

Communication specifications are indicated as below:

Serial Interface (I²C-bus);

Sending and receiving data through I^2C -bus that consists of two bus lines of a serial data line (SDA) and a serial clock line (SCL). This bus enables 8-bit bi-directional serial data to transmit at the maximum speed of 400kbits (fast mode). This is not compatible with Hs mode.

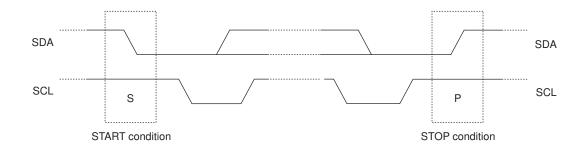
Terms used in I^2C

The following terms are used in I²C

Terms	Description		
Transmitter	Device to send data to the bus		
Receiver	Device to receive from the bus		
Master	Device to start data transmission, generate signal, and terminate data transmission		
Slave	Device of which address is designated master		

[Start] and [Stop] conditions

[Start] condition is required at the start of data communication and [Stop] condition at the end of data communication. The condition in which the SDA line changes from [H] to [L] with SCL at [H] is called the [Start] condition. The condition in which the SDA line changes from [L] to [H] with SCL at [H] is called the [Start] condition.

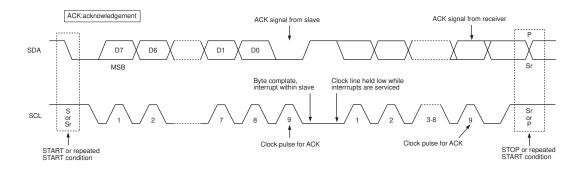


Data transmission

The length of each byte which is output to SDA line is always 8 bits. An acknowledge bit is needed after each byte. Data is transmitted sequentially from the most significant bit (MSB).

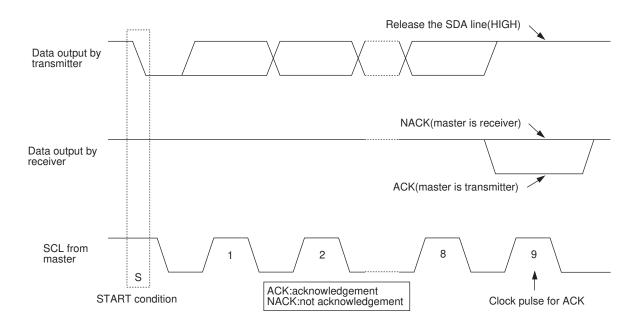
During the data transfer, the slave address is transmitted after the [Start] condition (S).

Data transfer is always ended by the [Stop] condition (P) generated by the master.



Acknowledge (Receive acknowledge)

When the master generates the acknowledge clock pulse, the transmitter opens the SDA line. (SDA line enters the [H] state.) When the acknowledge clock pulse is in the [H] state, the receiver sets the SDA line to [L] each time it receives one byte (eight bits) data. When the master works as a receiver, the master informs the slave of the end of data by omitting acknowledge at the end of data sent from the slave.

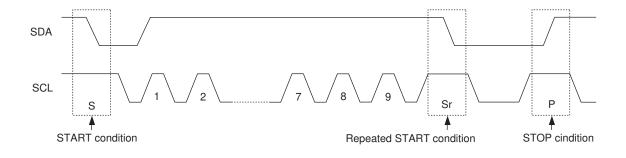


Software reset

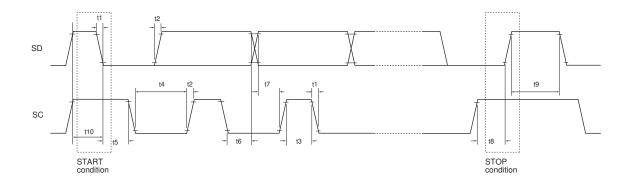
If the communication is interrupted (microcomputer reset, etc.), it is possible to communicate normally by entering the below signals and resetting the CPU in software.

*These signal timings restore the communication after its interruption. The register setting is never reset. *Software most accurate in a connectible with I^2C has format

*Software reset command is incompatible with I²C-bus format.



Electrical specification and timing for I/O stages



Bus line characteristics

Characteristic	Symbol	FAST-I	MODE	unit	Example at
		min	max		SCL = 100kHz
SCL clock frequency	fSCL		400	kHz	100
Fall time of SDA and SCL	t1	20+0.1Cb	300	ns	
Rise time of SDA and SCL	t2	20+0.1Cb	300	ns	
SCL "H" time	t3	0.6		μs	3
SCL "L" time	t4	1.3		μs	7
[Start] condition holding time	t5	0.6		μs	10
Data holding time for I ² C bus device	t6	0.3		μs	
Data setup time	t7	0.1		μs	3
[Stop] condition setup time	t8	0.6		μs	10
Bus free time between [Stop] and [Start]	t9	1.3		μs	20
[Start] condition setup time	t10	0.6		μs	
Bus line capacitive load	Cb		400	pF	

Serial interface voltage level

VDD: Communication bus voltage

Characteristic	min	max	unit
High level input voltage	0.7V _{DD}	V _{DD}	V
Low level input voltage	0.0	0.3V _{DD}	V
High level output voltage (open drain)	V _{DD}	*2	V
Low level output voltage (open drain)	0.0	0.2V _{DD}	V

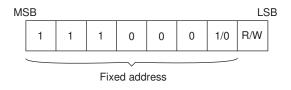
*2: Output impedance of open drain becomes high at the high level output voltage.

Output voltage equals to V_{DD} (voltage = V_{DD}) since drain is pulled up to V_{DD} .

Definition of each bit

1) Slave address

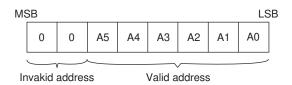
The slave address consists of seven-bit fixed address "1110000" or "1110001", which is unique to a chip, and the eighth-bit data direction bit(R/W). Sending (writing) is processed when the data direction bit is"0", and receiving (reading) is processed when it is "1". The fixed address is set to "1110001" at DEVAR=1 and it is set to "1110000" at DEVAR=0.



R/W	BIT
READ	1
WRITE	0

2) Register address

Since the total number of internal register is 34, 2-bit data set on the MSB side becomes invalid. 64 addresses are accepted 6 bits are used, but only 34 registers are used.



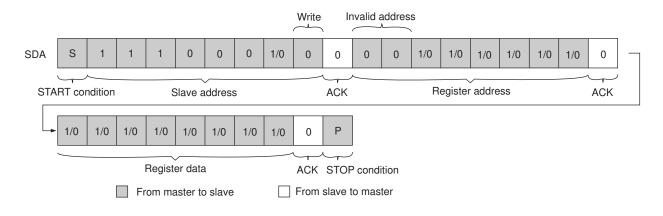
3) Register data

Each register data consists of eight bits.

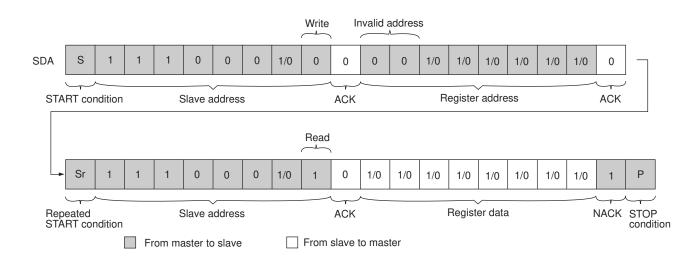
	D7	D6	D5	D4	D3	D2	D1	D0	
MS	MSB								SΒ

Command Format

1) Individual registers data writing



2) Individual registers data reading



Register Map 1 * HEX value is set by default.

Register		value is set by de		sed BIT	Read/	Binary	He
Register	BIT	Bit name	Function	Bit operation		-	
ddress	-				Write	value	valı
Dh	7					0	
	6	SD_SL[2]	SD level detection setting	0:DRS0 1:DRS1 2:DRS2 3:DRS3 4:DRS4 5:DRS5 6:DRS6 7:DRS7	R/W	0	
	5	SD_SL[1]			R/W	0	
	4	SD_SL[0]			R/W	0	h'
	3	DWAG[3]	Wide band AGC level setting	0:15.6mVp-p 1:31.3mVp-p 2:46.9mVp-p 3:62.5mVp-p 4:78.1mVp-p 5:93.8mVp-p 6:109.4mVp-p 7:125.0mVp-p	R/W	0	
	2	DWAG[2]		8:140.6mVp-p 9:156.3mVp-p 10:171.9mVp-p 11:187.5mVp-p	R/W	0	
	1	DWAG[1]		12:203.1mVp-p 13:218.8mVp-p 14:234.4mVp-p 15:250mVp-p	R/W	0	
	0	DWAG[0]			R/W	0	
01h	7					0	
	6					0	
	5					0	
	4					0	h'(
	3					0	
	2					0	
	1	IMSD_SL[1]	Unused			0	
	0	IMSD_SL[0]				0	
02h	7	CLKIN	XTAL current setting	1:Normal 0:Twice	R/W	1	
	6	DLOCKSEL	LOCKDET output waveform selection	1:Number of comparing 6 0:Munber of comparing 3	R/W	0	
	5		Phase comparison frequency selection	0:100kHz 1:50kHz 2:50kHz 3:25kHz	R/W	0	
		DFSEL[1]	r hase compansion nequency selection				
	4	DFSEL[0]			R/W	1	h's
	3	ENPE	Entire circuit enable	1:ON 0:OFF (Entire circuit OFF)	R/W	1	
	2	DNGA[2]	Narrow band AGC level setting	0:35mVp-p 1:111mVp-p 2:187mVp-p 3:263mVp-p 4:339mVp-p 5:415mVp-p 6:491mVp-p 7:567mVp-p	R/W	0	
	1	DNGA[1]		(When the setting value is ether 0 or 1 and MSK=4%, error is	R/W	0	
	0	DNGA[0]		detected in BER.)	R/W	1	
03h	7	ENCPLEVEL	Charge pump level comparison selection	1:ON 0:OFF	R/W	1	
	6	DENPRO	Program counter enable	1:0N 0:0FF	R/W	1	
							1 1 h'F
	5	DENPD	Phase comparison enable	1:0N 0:0FF	R/W		
	4	DENCP	Charge pump enable	1:ON 0:OFF	R/W	1	
	3	DENREF	S-meter enable	1:ON 0:OFF	R/W	1	
	2	DENXTAL	XTAL enable	1:ON 0:OFF	R/W	1	
	1	DEBDEMO	Demodulator enable	1:ON 0:OFF	R/W	1	
	0	ENFST	Complex BPF block, IF AGC block enable	1:ON 0:OFF	R/W	1	
04h	7	DENLEVELDET	Capacitor bank control circuit enable	1:ON 0:OFF	R/W	0	
0411	6	ENRFMIX	RFMIX enable	1:0N 0:0FF	R/W	1	
	5	ENIFLPF	IF LPF enable	1:0N 0:0FF	R/W	1	
	4	ENDET	Wide band AGC, Narrow band AGC block enable	1:ON 0:OFF	R/W	1	h'7
	3	ENLNA	LNA block enable	1:ON 0:OFF	R/W	1	
	2	DENSMETER	Reference counter enable	1:ON 0:OFF	R/W	1	
	1	DLOEN	Local oscillation enable	1:ON 0:OFF	R/W	1	
	0	DENPLL	PLL block enable	1:ON 0:OFF	R/W	1	
05h	7					0	
0011	6					0	
	5					0	
	4					0	h'(
	3					0	
	2					0	
	1	DNBAGC	IF AGC detection selector (Narrow band AGC)	1:ON 0:OFF	R/W	1	
	0	DWBAGC	RF AGC detection selector (Wide band AGC)	1:ON 0:OFF	R/W	1	
06h	7	DF0OSC[7]	Capacitor band value		R/W	1	
	6	DF0OSC[6]	Oscillation frequency adjustment for master time		R/W	0	
			constant setting				
	5	DF0OSC[5]			R/W	0	
	4	DF0OSC[4]			R/W	0	h'i
	3	DF0OSC[3]			R/W	0	
	2	DF0OSC[2]			R/W	0	
	1	DF0OSC[1]			R/W	0	
	0	DF0OSC[0]			R/W	0	
07h	7	DBPFO[7]	Capacitor bank value		R/W	1	
	6	DBPFO[6]	Complex BPF F0 adjustment		R/W	0	
	5	DBPFO[5]			R/W	0	
	4	DBPFO[4]			R/W	0	h'i
				1	1		
	3	DBPFO[3]			R/W	0	
	3	DBPFO[3] DBPFO[2]			R/W R/W	0	

Register Map 2 * HEX value is set by default.

address 08h 7 6 5 4 3 2 1 0 7 6 5 4 3 2 1 0 0 09h 7 6 5 4 3 2 1 0 0 0Ah 7 6 5 4 3 2 1 0 0 0Ah 7 6 5 4 3 2 1 0 0 0Bh 7 6 5 4 3 2 1 0 0 0Ch 7 6 5 7 6 5 5 4 3 1 0	BITBit name7D2BPF[7]6D2BPF[6]5D2BPF[7]4D2BPF[1]0D2BPF[1]0D2BPF[1]0D2BPF[0]1D2BPF[1]0D2BPF[1]0D2BPF[1]1D2BPF[1]1D2BPF[1]1D2BPF[0]3DDEMOG[1]4DDEMOG[1]3DMONOC[3]1DMONOC[1]0DMONOC[1]1DMONOC[1]1DMONOC[1]1DMONOC[1]1DMONOC[1]1DMONOC[1]1DMONOC[2]1DMONOC[2]1DMONOC[1]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]1DMONOC[2]2DMONOC[2]3DMONOC[2]3DMONOC[2]4DMONOC[2]4DMONOC[2]5DMONOC[2]4DMONOC[2]5DMONOC[2]6DMONOC[2]7<	Function Capacitor bank value 2 nd IF BPF 10 adjustment DLL demodulator loop gain setting DLL demodulator loop gain setting Mono multi center setting I Complex BPF injection changeover IO balance adjustment	Bit operation Bit operation Discrete State Sta	Read/ Write R/W R/W	Binary value 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 1 1 0	Hex value h'80 h'17 h'17 h'02
address 7 08h 7 6 5 4 3 2 1 0 7 6 5 4 3 2 1 0 7 6 5 4 3 2 1 0 0 0Ah 7 6 5 4 3 2 1 0 0 0Bh 7 6 5 4 3 2 1 0 0 0Bh 7 6 5 4 3 2 1 0 0 0Ch 7 6 5 4 3 2 1 0 0 0Ch 7 6	7 D2BPF[7] 6 D2BPF[6] 5 D2BPF[6] 4 D2BPF[1] 3 D2BPF[2] 1 D2BPF[1] 0 D2BPF[0] 7 D2BPF[0] 7 D2BPF[0] 7 D2BPF[0] 7 D2BPF[0] 7 D2BPG[0] 6 D2BPG[0] 7 D2BPG[0] 8 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 0 DMONOC[2] 1 DMONOC[2] 7 Image: Comparison of the second of the sec	Capacitor bank value 2 nd IF BPF f0 adjustment DLL demodulator loop gain setting DLL demodulator loop gain setting Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W	1 0 0 0 0 0 0 0 0 0 1 1 0 0 0 0 0 0 0 0	h'80 h'17 h'02
6 5 4 3 2 1 0 09h 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 1 0 0Bh 7 6 5 4 3 2 1 0 0Bh 7 6 5 4 3 2 1 0 0Ch <	6 D2BPF[6] 5 D2BPF[5] 4 D2BPF[1] 2 D2BPF[2] 1 D2BPF[1] 0 D2BPF[1] 0 D2BPF[0] 7 - 6 - 5 DDEMOG[1] 4 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[1] 0 DMONOC[1] 0 DMONOC[2] 1 DMONOC[1] 0 DMONOC[1] 1 ENIMRSSI 0 DICC 7 - 6 DBL[6] 5 DBL[5] 4 DBL[2] 1 DBL[1]	2 nd IF BPF 10 adjustment DLL demodulator loop gain setting Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W	0 0 0 0 0 0 0 0 0 1 1 0 0 0 0 0 0 0 0 0	h'17 h'02
5 4 3 2 1 0 09h 7 6 5 4 33 22 1 0 0Ah 7 6 5 4 33 22 1 0 0Ah 7 6 5 4 33 2 1 0 0Bh 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3 2 1 0 0Ch 7	5 D2BPF[5] 4 D2BPF[4] 3 D2BPF[3] 2 D2BPF[2] 1 D2BPF[1] 0 D2BPF[0] 7 - 6 - 5 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[1] 0 DMONOC[2] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 DMONOC[2] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 ENIMRSSI 0 DICC 7 - 6 DBL[6] 5 DBL[5] 4 DBL[3] 2 DBL[2] 1 DBL[1]	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W	0 0 0 0 0 0 0 1 1 0 1 1 1 1 1 1 0 0 0 0	h'17 h'02
4 3 2 1 0 09h 7 6 5 4 33 22 1 00 0Ah 7 6 5 4 33 22 1 0 0Ah 7 6 5 4 33 22 1 0 0Bh 7 6 5 4 33 2 1 0 0Bh 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3 1 0 <	4 D2BPF[4] 3 D2BPF[3] 2 D2BPF[2] 1 D2BPF[1] 0 D2BPF[0] 7 - 6 - 5 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[1] 0 DMONOC[1] 0 DMONOC[2] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 ENIMRSSI 0 DICC 7 - 6 DBL[6] 5 DBL[5] 4 DBL[3] 2 DBL[2] 1 DBL[1]	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W	0 0 0 0 0 0 1 1 0 1 1 1 1 1 1 0 0 0 0 0	h'17 h'02
3 2 1 0 09h 7 6 5 4 33 22 1 00 0Ah 7 66 55 44 33 22 1 0 0Ah 7 6 5 4 33 2 1 0 0Bh 7 6 5 4 33 2 1 0 0Bh 7 6 5 4 3 0 0Ch 7 6 5 4 3	3 D2BPF[3] 2 D2BPF[2] 1 D2BPF[1] 0 D2BPF[0] 7 D2BPF[0] 6 5 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[1] 0 DMONOC[1] 0 DMONOC[2] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 DMONOC[2] 1 DMONOC[2] 1 DMONOC[2] 1 DMONOC[1] 0 DMONOC[2] 1 DMONOC[2] 1 DMONOC[2] 1 DMONOC[2] 1 DMONOC[2] 1 DMONOC[2] 2 DMONOC[2] 3 DMONOC[2] 1 ENIMRSSI 0 DICC 7 DBL[6] 5 DBL[5] 4 DBL[2]	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W R/W R/W R/W	0 0 0 0 0 1 1 0 1 1 1 1 1 1 0 0 0 0 0 0	h'17 h'02
2 1 0 09h 7 6 5 4 3 2 1 0 00h 7 6 5 4 3 2 1 0 00h 7 6 5 4 3 2 1 0 00h 7 6 5 4 3 2 1 0 00h 7 6 5 4 3 2 1 0 0 00h 7 6 5 4 3 2 1 0 0 00h 7 6 5 4 3 2 1 0 0 00h 7 6 5 4 3 2 1 0 0 00h 7 6 5 4 3 3 2 1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	2 D2BPF[2] 1 D2BPF[1] 0 D2BPF[0] 7 - 6 - 5 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[3] 2 DMONOC[1] 0 DMONOC[2] 1 DMONOC[2] 1 DMONOC[1] 0 DMONOC[2] 1 DMONOC[2] 1 DMONOC[1] 0 DMONOC[2] 1 DMONOC[2] 2 DMONOC[2] 3 DIOC 7 DBL[6] 5 DBL[5] 4 DBL[2] 1 DBL[1]	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W R/W R/W R/W	0 0 0 0 1 1 0 1 1 1 1 1 1 0 0 0 0 0 0 0	h'02
09h 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 1 0 0Bh 7 6 5 4 3 2 1 0 0 0Bh 7 7 6 5 5 4 3 2 1 0 0 0 0 0 7 6 5 5 4 3 2 1 0 0 0 0 0 1 7 7 6 5 5 1 9 1 0 0 0 0 0 0 1 7 1 0 0 0 0 0 0 1 7 6 6 5 5 1 9 1 0 0 0 0 0 0 1 7 1 0 0 0 0 0 0 0 1 1 1 0 0 0 0	1 D2BPF[1] 0 D2BPF[0] 7 - 6 - 5 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[3] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 ENIMRS 2 Image: Comparison of the second of the sec	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W R/W R/W R/W	0 0 0 1 1 0 1 1 1 1 1 0 0 0 0 0 0 0 0 0	h'02
09h 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 2 1 0 0 0Bh 7 6 5 4 3 2 2 1 0 0 0Bh 7 7 6 5 5 4 4 3 2 2 1 0 0 0 0 6 5 5 4 4 3 3 2 2 1 0 0 0 0 7 6 5 5 5 5 5 6 6 5 5 9 6 6 5 5 9 7 8 9 6 6 5 5 9 7 8 9 7 8 9 7 8 9 7 8 9 7 8 9 8 9 8 9	0 D2BPF[0] 7 6 5 DDEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[2] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 DMONOC[1] 0 DMONOC[1] 0 DMONOC[1] 1 DMONOC[1] 0 DMONOC[1] 1 DMONOC[1] 1 DMONOC[1] 0 DMONOC[1] 1 DMONOC[1] 1 DMONOC[1] 2 Image: Comparison of the property o	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W	0 0 0 1 1 1 1 1 1 0 0 0 0 0 0 0 0 0 0 0	h'02
09h 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 1 0 0Ah 7 6 5 4 3 2 2 1 0 0 0Bh 7 6 5 4 3 2 2 1 0 0 0Bh 7 6 5 5 4 4 3 2 2 1 0 0 0 0 1 7 6 6 5 5 5 4 4 3 3 2 2 1 0 0 0 0 1 7 6 6 5 5 5 4 4 3 3 2 2 1 0 0 0 0 1 7 6 6 5 5 5 4 4 3 2 2 1 0 0 0 1 1 0 0 0 1 1 0 0 1 1 0 0 1 0 1 0 0 1 0 0 1 0 1 0 0 1 0 1 0 0 1 0 0 1 0 0 1 0 0 1 0 0 1 0	7	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W R/W R/W R/W	0 0 0 1 1 1 1 1 0 0 0 0 0 0 0 0 0 0 0 0	h'02
0Ah 7 0Ah 7 0Ah 7 0 0Ah 7 0 0Bh 7 6 5 4 3 2 1 0 0 0 6 5 4 3 2 1 0 0 0 6 5 4 3 2 1 0 0 0 6 5 4 3 2 1 0 0 0 0 0 0 0 0 0 0 0 0 0	6 DEMOG[1] 4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[1] 0 DMONOC[1] 0 DMONOC[0] 7 1 6 1 5 1 4 1 3 1 2 1 4 1 3 1 2 1 4 1 3 1 2 1 4 1 3 1 2 1 4 1 3 1 7 1 6 10C 7 1 6 10EL[6] 5 0BL[6] 5 0BL[3] 2 0BL[2] 1 0BL[1]	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W	0 0 1 0 1 1 1 0 0 0 0 0 0 0 0 0 0 0 0 0	h'02
0Ah 7 0Ah 7 6 5 4 3 2 1 0 0 0 0 0 0 0 0 0 0 0 0 0	4 DDEMOG[0] 3 DMONOC[3] 2 DMONOC[2] 1 DMONOC[1] 0 DMONOC[0] 7 Image: Comparison of the second of the se	Mono multi center setting Mono multi center setting XTAL OSC FET size setting Complex BPF injection changeover		R/W	0 1 0 1 1 1 0 0 0 0 0 0 0 0 0 1 0 0 1 0 0 1 0	h'02
0Ah 7 6 5 4 3 2 1 0 5 4 3 2 1 0 0 0 0 0 0 0 0 0 0 0 0 0	3 DMONOC[3] 2 DMONOC[2] 1 DMONOC[1] 0 DMONOC[0] 7 6 5 4 3 2 1 ENIMRSSI 0 DIQC 7 6 DBL[6] 5 DBL[5] 4 DBL[3] 2 DBL[2]	XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W R/W R/W R/W	0 1 1 0 0 0 0 0 0 1 0 0 1 0 0 1 0 0 0 0	h'02
0Ah 7 6 5 4 3 2 1 0 0 0 0 0 0 0 0 0 0 0 0 0	2 DMONOC[2] 1 DMONOC[1] 0 DMONOC[0] 7	XTAL OSC FET size setting Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W R/W R/W R/W	1 1 1 0 0 0 0 0 1 0 0 1 0 0 1 0 0 0 1 0	h'02
0Ah 7 6 5 4 3 2 1 0 0Bh 7 6 5 4 3 2 1 0 0 6 5 4 3 2 1 0 0 0 5 5 4 3 2 1 0 0 0 0 1 7 6 5 5 4 3 3 2 1 0 0 0 0 8 1 7 1 0 0 0 1 7 1 9 1 0 1 0 1 9 1 1 0 0 1 9 1 1 0 1 0 1	1 DMONOC[1] 0 DMONOC[0] 7 6 5 4 3 2 1 ENIMRSSI 0 DIQC 7 6 DBL[6] 5 DBL[5] 4 DBL[3] 2 DBL[2] 1 DBL[1]	Complex BPF injection changeover		R/W	1 1 0 0 0 0 0 1 0 1 0 0 1 0 0 0 0 0 0 0 0 0 0 0 0 0	
0Ah 7 6 5 4 3 2 1 0 0Bh 7 6 5 4 3 2 4 3 2 1 0 0 0Ch 7 6 5 5 4 3 2 2 1 0 0 0Ch 7 7 6 5 5 4 3 3 2 2 1 0 0 5 5 4 3 1 0 0 5 5 5 4 4 3 3 2 2 1 1 0 0 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5	0 DMONOC[0] 7	Complex BPF injection changeover		R.W 	1 0 0 0 0 1 1 0 0 1 0 0 1 0 0 0 0 0	
0Ah 7 6 5 4 3 2 1 0 0 0 Bh 7 6 5 4 3 2 2 1 0 0 Bh 7 6 5 5 4 4 3 2 2 1 0 0 0 Ch 7 6 5 5 4 3 2 2 1 0 0 0 5 5 4 3 3 2 2 1 0 0 0 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5	7	Complex BPF injection changeover		R/W R/W R/W R/W R/W R/W R/W	0 0 0 0 1 0 1 0 0 1 0 0 0 0 0 0	
0Bh 7 6 5 1 0 0Bh 7 6 5 4 3 2 1 0 0 0Ch 7 6 5 4 3 2 2 1 0 0 0Ch 7 6 5 5 4 3 2 2 1 1 0 0 5 5 4 3 3 2 2 1 1 0 0 0 5 5 5 5 5 5 1 1 0 0 0 5 5 5 5	6 Image: Second system 5 Image: Second system 4 Image: Second system 2 Image: Second system 1 ENIMRSSI 0 DIQC 7 Image: Second system 6 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[2] 1 DBL[1]	Complex BPF injection changeover		R/W R/W R/W R/W	0 0 0 1 0 1 0 0 1 0 0 0 0 0 0	
0Bh 7 6 5 6 5 4 3 0 6 5 4 3 2 1 0 0 0Ch 7 6 5 4 3 2 2 1 0 0 0Ch 7 6 5 5 4 3 2 2 1 0 0 0 1 3 3 2 2 1 0 0 1 0 0 0 1 1 0 0 0 1 1 0 0 0 1 1 0 0 0 1 0 0 0 1 0 0 0 0 0 1 0 0 0 0 1 0	5 Image: Second system 4 Image: Second system 2 Image: Second system 1 ENIMRSSI 0 DIQC 7 Image: Second system 6 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]	Complex BPF injection changeover		R/W R/W R/W R/W	0 0 0 1 0 0 1 0 0 0 0	
4 3 2 1 0 0 0Bh 7 6 5 4 3 2 1 0 0 0Ch 7 6 5 4 3 3 2 1 0 0 0Ch 7 6 5 4 3 3 2 1 0 0 0 0 1 3 3 3 3 3 3 3 3 3 3 3 3 3 3	4	Complex BPF injection changeover		R/W R/W R/W R/W	0 0 1 0 0 1 0 0 0 0 0	
0Bh 7 6 5 4 3 2 1 6 5 4 3 2 1 0 0 0Ch 7 6 5 4 3 3 2 1 0 0 0Ch 3 7 6 5 5 4 3 3 2 1 1 0 0 0 1 0 0 0 1 0 0 0 0 0 0 0 0 0	3	Complex BPF injection changeover		R/W R/W R/W R/W	0 0 1 0 0 1 0 0 0 0	
2 1 0 0Bh 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3 2 1 0 0 0Ch 7 6 5 4 3 3 2 1 0 0 1 1 0 0 1 1 1 1 0 1 1 1 1 1 1 1	2 ENIMRSSI 0 DIQC 7 6 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]	Complex BPF injection changeover		R/W R/W R/W R/W	0 1 0 0 1 0 0 0 0	
0Bh 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3 3 2 4 3 3 4 3 3 4 3 3 1 0 0 1 1 0 1 0 1 1 0 1 1 1 0 1 1 1 1	1 ENIMRSSI 0 DIQC 7 - 6 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]	Complex BPF injection changeover		R/W R/W R/W R/W	1 0 0 1 0 0 0	h'40
0Bh 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3	0 DIQC 7 6 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]	Complex BPF injection changeover		R/W R/W R/W R/W	0 0 1 0 0 0	h'40
0Bh 7 6 5 4 3 2 1 0 0Ch 7 6 5 4 3	7 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]		1:lower 0:upper	R/W R/W R/W R/W	0 1 0 0	h'40
6 5 4 3 2 1 0 0 0 Ch 7 6 5 4 4 3	6 DBL[6] 5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]	IQ balance adjustment		R/W R/W R/W	1 0 0	h'40
0Ch 7 6 3 0Ch 7 6 3 4 3	5 DBL[5] 4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]	IQ balance adjustment		R/W R/W R/W	0 0 0	h'40
4 3 2 1 0 0 0 0 0 0 0 0 0 0 0 0 0 7 6 5 5 4 4 3	4 DBL[4] 3 DBL[3] 2 DBL[2] 1 DBL[1]			R/W R/W	0	h'40
0Ch 7 6 5 4 3	3 DBL[3] 2 DBL[2] 1 DBL[1]			R/W	0	h'40
2 1 0 0 0 0 0 0 0 0 0 0 7 6 5 5 4 4 3	2 DBL[2] 1 DBL[1]					
0Ch 7 6 5 4 3	1 DBL[1]			R/VV		
0 0Ch 7 6 5 4 3				R/W	0	
0Ch 7 6 5 4 3	U DBL[U]			R/W	0	
6 5 4 3	7			10.00	0	
5 4 3	6				0	
4	5				0	
3	4				0	
2	3 DCP1REF[3]	Charge pump output current value setting	0:0.1mA 1:0.2mA 2:0.3mA 3:0.4mA 4:0.5mA 5:0.6mA 6:0.7mA	R/W	1	h'0A
2	2 DCP1REF[2]		7:0.8mA 8:0.9mA A:1mA B:1.1mA C:1.2mA D: unused	R/W	0	
1	1 DCP1REF[1]		E: unused F: unused	R/W	1	1
0	0 DCP1REF[0]			R/W	0	
0Dh 7	7 DPCNT_L[7]	N value of frequency divider (low 8 bits)		R/W	•	
6	6 DPCNT_L[6]	N value of frequency divider = ((4 × received frequency)±(4 × 1 st IF frequency)) /		R/W	•	
5	5 DPCNT_L[5]	(4 channel × step frequency)		R/W	•	
4	4 DPCNT_L[4]	* 1 st IF frequency is 1.2MHz		R/W	*	h'**
	3 DPCNT_L[3]			R/W	•	
2	2 DPCNT_L[2]			R/W	•	
	1 DPCNT_L[1]			R/W	•	
	0 DPCNT_L[0]			R/W	*	
	7 DPCNT_H[7]	N value of frequency divider (high 8 bits)		R/W	*	
	6 DPCNT_H[6]			R/W	•	
	5 DPCNT_H[5]			R/W	•	
	4 DPCNT_H[4]			R/W		h'**
	3 DPCNT_H[3]			R/W	•	
	2 DPCNT_H[2]			R/W	*	
	1 DPCNT_H[1] 0 DPCNT_H[0]			R/W R/W		
		Local oscillator capacitor bank sotting (low 9 bits)		R/W	0	
	7 DCBANK_L[7] 6 DCBANK_L[6]	Local oscillator capacitor bank setting (low 8 bits)		R/W	0	
	5 DCBANK_L[5]			R/W	0	
	4 DCBANK_L[5]			R/W	0	
	- DODAININ_L[4]			R/W	0	h'00
			1	D/ W		
0	3 DCBANK_L[3]			R/M		
	3 DCBANK_L[3] 2 DCBANK_L[2] 1 DCBANK_L[1]			R/W R/W	0	

Register	BIT	Bit name	Function	Bit operation	Read/	Binary	Hex
address		Dit fiame	Function		Write	value	valu
Dh	7					0	
	6 5					0	
	4					0	
	3					0	h'(
	2					0	
	1					0	
	0	DCBANK_H[8]	Local oscillator capacitor bank setting (high 1 bit)		R/W	1	
1h	7					0	
	6					0	
	5					0	
	4	DCBEN	Unused			0	h'C
	3	DLOALC[3]	Local oscillation level setting		R/W	1	•
	2	DLOALC[2] DLOALC[1]			R/W R/W	1	•
	1	DLOALC[1]			R/W	1	
l2h	7	DEOREO[0]			10.00	0	
	6	DENIFCOUNT	Frequency counter (analog block) enable	1:ON 0:OFF	R/W	0	
	5	DENF0OSC	f0 detection oscillation circuit enable	1:ON 0:OFF	R/W	0	
	4	DENIFFREQ	Logic part reference clock enable	1:ON 0:OFF	R/W	0	
	3					0	h'(
	2	DSCTCOUNT[2]	Count frequency selection	0:unused 1:IF frequency 2:prescaler frequency	R/W	0	
	1	DSCTCOUNT[1]		3:freacaler frequency 4:f0 detection oscillation frequency 5:f0 detection oscillation frequency 6:unused 7:IF frequency	R/W	0	
	0	DSCTCOUNT[0]			R/W	0	1
13h	7					0	
	6					0	
	5					0	
	4					0	h'(
	3	OTE		1.0N/(fragmanning starts) Objects to 0 automatically	R/W	0	
	1	CTE GT[1]	Counter start trigger	1:ON (frequency counter start) Charge to 0 automatically 0:4ms 1:8ms 2:32ms 3:64ms	R/W	0	
	0	GT[0]	Frequency counter gate time selection	0.4115 1.0115 2.32115 3.04115	R/W	1	
14h	7	LOFQ_L[7]	LO_COUNT value (low 8 bits)		R	*	
	6	LOFQ_L[6]	Measurement frequency = counter value / GT[ms]		R	•	ľ
	5	LOFQ_L[5]			R	*	
	4	LOFQ_L[4]			R	*	1
	3	LOFQ_L[3]			R	*	h'C
	2	LOFQ_L[2]			R	•	
	1	LOFQ_L[1]			R	*	l.
	0	LOFQ_L[0]			R	*	
15h	7	LOFQ_H[7]	LO_COUNT value (upper 8 bits)		R	•	
	6	LOFQ_H[6]			R	•	
	5	LOFQ_H[5]			R	•	
	4	LOFQ_H[4]			R	*	h'C
	3	LOFQ_H[3]			R		
	2	LOFQ_H[2] LOFQ_H[1]			R		
	0	LOFQ_H[I]			R		
16h	7					0	
	6					0	1
	5	COUNTSEL				0	
	4	LOCKDETSEL				1	h'1
	3	LOCKDET_DIG				0	
	2	LOCKDET	LOCK detection	1:LOCK 0:UNLOCK	R/W	0	
	1	PHLEVEL[1]	Charge pump voltage level detection	0:less than 0.5V 1:0.5V to 2.8V 2:Unused 3:more than 2.8V	R/W	0	
	0	PHLEVEL[0]			R/W	0	
17h	7					*	
	6					*	
	5					*	
	4	IMPOSIO	Posset detection aircuit	Orreast dimensional distance	P	*	h'(
	3	IMRSSI[3]	Reset detection circuit	0:reset 1:reset cancellation	R	*	
	2	IMRSSI[2]			R R		ł
	1	IMRSSI[1]					

Register Map 4

* HEX value is set by default.

: Unused BIT

Register		value is set by de	efault. Unused		Read/	Binary	Hex
address	BIT	Bit name	Function	Bit operation	Write	value	value
18h	7					0	
	6	DRS[6]	S-meter detection level	Detection range can be changed by setting to DNGA (02h)	R	•	
	5	DRS[5]			R	•	
	4	DRS[4]			R	•	h'**
	3	DRS[3]			R	•	
	2	DRS[2]			R	*	
	1	DRS[1]			R	•	
19h	0	DRS[0] IFCOUNT_L[7]	IF count value (low 8 bits)		R		
190	7	IFCOUNT_L[7]	2 nd IF frequency measurement results		R		
	5	IFCOUNT_L[5]			R		
	4	IFCOUNT_L[4]			R		
	3	IFCOUNT_L[3]			R	*	h'**
	2	IFCOUNT_L[2]			R		
	1	IFCOUNT_L[1]			R	*	
	0	IFCOUNT_L[0]			R	*	
1Ah	7	IFCOUNT_H[7]	IF count value (high 8 bits)		R	•	
	6	IFCOUNT_H[6]			R	•	
	5	IFCOUNT_H[5]			R	•	
	4	IFCOUNT_H[4]			R	*	h'**
	3	IFCOUNT_H[3]			R	•	
	2	IFCOUNT_H[2]			R	•	
	1	IFCOUNT_H[1]			R	•	
105	0	IFCOUNT_H[0]			R	*	
1Bh	7		Unused		R		
		IMCOUNT_L[6] IMCOUNT_L[5]			R		
		IMCOUNT_L[4]			R	*	
		IMCOUNT_L[3]			R	•	h'**
	2	IMCOUNT_L[2]			R	*	
		IMCOUNT_L[1]			R	*	
	0	IMCOUNT_L[0]			R	*	
1Ch	7	IMCOUNT_H[7]	Unused		R		
	6	IMCOUNT_H[6]			R	•	
	5	IMCOUNT_H[5]			R	•	
	4	IMCOUNT_H[4]			R	*	h'**
	3	IMCOUNT_H[3]			R	•	
	2	IMCOUNT_H[2]			R	•	
		IMCOUNT_H[1]			R	*	
1Dh	0	IMCOUNT_H[0] F0_L[7]	f0 detection oscillation frequency count value (low 8 bits)		R		
TDI	6	F0_L[6]	Frequency measurement result for master time constant		R	*	
		F0_L[5]	setting		R		
	4	F0_L[4]			R		
		F0_L[3]			R	*	h'**
	2	F0_L[2]			R	*	
		F0_L[1]			R	•	
	0	F0_L[0]			R	*	
1Eh	7	F0_H[7]	f0 detection oscillation frequency count value (high 8 bits)		R		
	6	F0_H[6]	Site		R	•	
		F0_H[5]			R		
		F0_H[4]			R	•	h'**
		F0_H[3]			R	•	
	2	F0_H[2]			R	•	
		F0_H[1]			R		
1Fh	0	F0_H[0]			R	0	
	6					0	
	5					0	
	4					0	
	3					0	h'02
	2	DOUTSEL	Register for TEST		R/W	0	
	1	DCNTEST	Register for TEST		R/W	1	
	0	DOUTTEST	Register for TEST		R/W	0	
					Contin	ued on ne	

Continued from preceding page.

Register	BIT	Diana	E suite		Read/	Binary	Hex
address	BH	Bit name	Function	Bit operation	Write	value	value
20h	7					0	
	6	ERR2	Local oscillator capacitor bank control error flag 2		R/W	0	
	5	ERR1	Local oscillator capacitor bank control error flag 1		R/W	0	
	4	DCOSEL2	Local oscillator capacitor bank value changeover	1:cap bank control value 0:l ² C input value	R/W	0	
	3	DCOSEL1	Local oscillator capacitor bank control process changeover	1:correcting process after sequential comparison 0:No correcting process after sequential comparison	R/W	1	h'0A
	2	DCOSEL0	Local oscillator capacitor bank control process changeover (micro alignment)	1:micro adjustment process 0:No micro adjustment process	R/W	0	
	1	DWAITSEL[1]	PLL operation check wait time after local oscillator capacitor bank adjustment	0:200µs 1:400µs 2:800µs 3:1600µs	R/W	1	
	0	DWAITSEL[0]	capacitor bank adjustment		R/W	0	
21h	7					0	
	6					0	
	5	DENINT	Register for TEST		R/W	0	
	4	MASKSEL	Register for TEST		R/W	0	
	3	LOSEL	Register for TEST		R/W	1	h'0A
	2	INTPH	Register for TEST		R/W	0	
	1	INTIM	Register for TEST		R/W	1	
	0	INTLO	Register for TEST		R/W	0	
22h	7	TESTSEL[2]	Register for TEST		R/W	0	
	6	TESTSEL[1]	Register for TEST		R/W	0	
	5	TESTSEL[0]	Register for TEST		R/W	0	
	4	DSW	PLL loop filter ON/OFF	1:ON 0:OFF	R/W	1	
	3	TIMESEL2[1]	Local oscillator capacitor bank control correcting circuit	0:200µs 1:400µs 2:800µs 3:1600µs	R/W	0	h'15
	2	TIMESEL2[0]	operation clock setting		R/W	1	
	1	TIMESEL[1]	Local oscillator capacitor bank control sequential	0:10µs 1:20µs 2:40µs 3:80µs	R/W	0	
	0	TIMESEL[0]	comparison control operation clock setting		R/W	1	

SD pin specification

SD voltage level VDD: supply voltage

item	min	max	unit
High level output voltage	V _{DD} -0.8	V _{DD}	v
Low level output voltage	0	0.4	v

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